

FFH50US60S 50 A, 600 V, STEALTH™ Diode

Features

- Stealth Recovery, t_{rr} = 113 ns (@ I_F = 50 A)
- Max Forward Voltage, V_F = 1.54 V (@ T_C = 25°C)
- · 600V Reverse Voltage and High Reliability
- · Operating Temperature = 175°C
- · Avalanche Energy Rated
- · RoHS Compliant

Applications

- SMPS, Welders
- Power Factor Correction
- · Uninterruptible Power Supplies
- Motor Drives

Description

The FFH50US60S is a STEALTHTM diode optimized for low loss performance in output rectification. The STEALTHTM family exhibits low reverse recovery current (I_{RR}), low V_F and soft recovery under typical operating conditions. This device is intended for use as an output rectification diode in Telecom power supplies and other power switching applications. Lower V_F and I_{RR} reduces diode losses. Formerly developmental type TA49468.

Package JEDEC STYLE 2 LEAD TO-247 ANODE CATHODE (BOTTOM SIDE METAL)

Device Maximum Ratings $T_C = 25$ °C unless otherwise noted

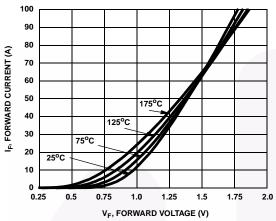
Symbol	Parameter	Rating	Unit	
V_{RRM}	Repetitive Peak Reverse Voltage	600	V	
V _{RWM}	Working Peak Reverse Voltage	600	V	
V _R	DC Blocking Voltage	600	V	
I _{F(AV)}	Average Rectified Forward Current (T _C = 120°C)	50	Α	
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	100	Α	
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60 Hz)	500	Α	
P _D	Power Dissipation	200	W	
E _{AVL}	Avalanche Energy (1 A, 40 mH)	20	mJ	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 175	°C	
TL	Maximum Temperature for Soldering	300	°C	
T _{PKG}	Leads at 0.063 in (1.6mm) from Case for 10 s Package Body for 10s, See Application Note AN-7528	260	°C	

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Device Ma	rking	Device	Package	Packing Meth	ode	Reel Size	Tape	Width	Qua	antity
FFH50US60S		FFH50US60S	TO247-2L	Tube		N/A	N/A		30	
Electric	al Ch	aracteristic	S T _C = 25°C (unless otherwise	noted	d			·	
Symbol	Parameter		Test Conditions		Min	Тур	Max	Unit		
Off State	Chara	cteristics						•		•
I _R	Instantaneous Reverse Current		<u> </u>	Т	_C = 25°C	-	-	100	μA	
-K					_C = 125°C	-	-	1	mA	
n State	Chara	cteristics				-	L	u.		
V _F	Instantaneous Forward Vo		oltage	I _F = 50 A	Т	_C = 25°C	-	1.38	1.54	V
* F	motante	inocao i ci wara v	onago	1F = 00 / t		C = 125°C	-	1.37	1.53	V
C _J		cteristics n Capacitance		V _R = 10 V, I _F = 0	0 A		-	110	-	pF
				VR = 10 V, IF = 0	<u> </u>			110		рі
		acteristics		TI 4 A AI /A+	100.0	\/\.\.\\ 1E\\/		47	80	
^L rr	t _{rr} Reverse Recovery Time			$I_F = 1 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 15 \text{ V}$ $I_F = 50 \text{ A}, dI_F/dt = 100 \text{ A/}\mu\text{s}, V_R = 15 \text{ V}$			- / -	75	124	ns
t _{rr}	Reverse Recovery Time		$I_F = 50 \text{ A}$, $I_F/I_R = 100 \text{ A/}\mu\text{s}$, $V_R = 13 \text{ A/}\mu\text{s}$, $V_R = 300 \text{ A/}\mu\text{s}$, $V_R = 390 \text{ V}$, $V_R = 25^{\circ}\text{C}$			-	113	-	ns	
I _{RR}	Reverse Recovery Current Reverse Recovered Charge						9.6	_	A	
Q _{RR}						-	0.9	-	μC	
T _{rr}		Recovery Time	9-	I _F = 50 A, dI _F /dt = 200 A/μs,		-	235	_	ns	
S		s Factor (t _b /t _a)				-	1.5	-	-	
I _{RR}		erse Recovery Current		$V_R = 390V$				15	-	Α
Q _{RR}	Reverse	Recovered Char	ge	$T_C = 125$ °C			-	2.3	-	μC
t _{rr}	Reverse	e Recovery Time		$I_F = 50 \text{ A},$ $dI_F/dt = 1000 \text{ A/}\mu\text{s},$			-	110	-	ns
S	Softnes	s Factor (t _b /t _a)					-	0.8	-	-
I _{RR}	Reverse	e Recovery Curre	nt	$V_R = 390 \text{ V},$		-	46	-	Α	
Q_{RR}	Reverse	e Recovered Char	ge	T _C = 125°C			-	3.1	-	μC
dI _M /dt	Maximu	ım di/dt during t _b					-	1000	-	A/µs
hermal	Charac	cteristics								
$R_{\theta JC}$	Thermal Resistance Junction to Case						-	-	0.75	°C/W
$R_{\theta JA}$	Thermal Resistance Junction to Ambient			TO-247			-	-	30	°C/W

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Typical Performance Curves



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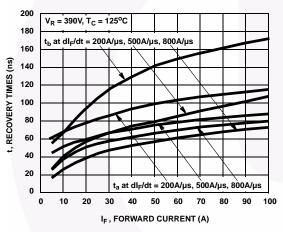
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Figure 1. Forward Current vs Forward Voltage

Figure 2. Reverse Current vs Reverse Voltage



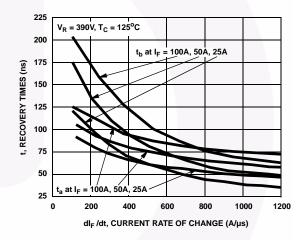
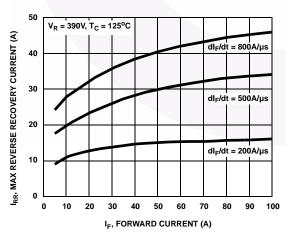


Figure 3. t_a and t_b Curves vs Forward Current

Figure 4. t_a and t_b Curves vs dl_F/dt



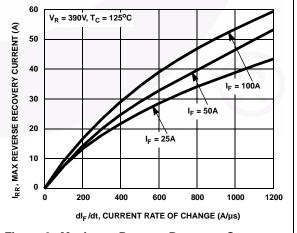


Figure 5. Maximum Reverse Recovery Current vs Forward Current

Figure 6. Maximum Reverse Recovery Current vs dI_F/dt

Typical Performance Curves (Continued) V_R = 390V, T_C = 125°C SOFTNESS FACTOR 2.2 2.0 1.8 _F = 100A 1.6 I_F = 50A REVERSE RECOVERY 1.4 I_F = 25A 1.2 1.0 0.8 ú 0.6 600 1200

Figure 7. Reverse Recovery Softness Factor vs $\mathrm{dI_F/dt}$

dI_F/dt, CURRENT RATE OF CHANGE (A/μs)

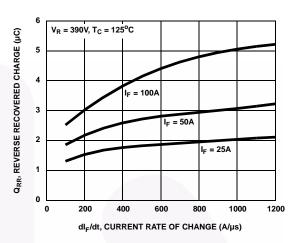


Figure 8. Reverse Recovery Charge vs dl_F/dt

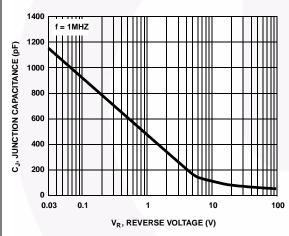


Figure 9. Junction Capacitance vs Reverse Voltage

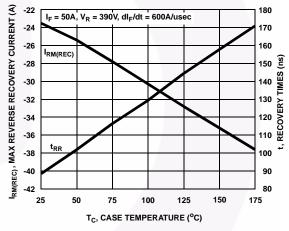


Figure 10. Maximum Reverse Recovery Current and t_{rr} vs Case Temperature

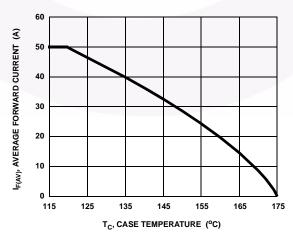


Figure 11. DC CURRENT DERATING CURVE

Typical Performance Curves (Continued)

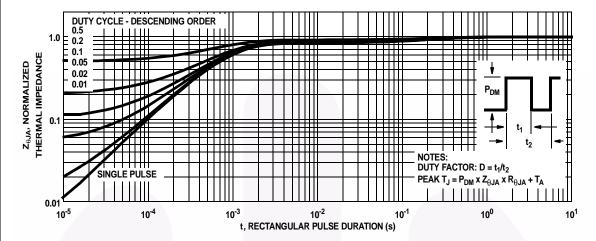


Figure 12. Normalized Maximum Transient Thermal Impedance

Test Circuit and Waveforms

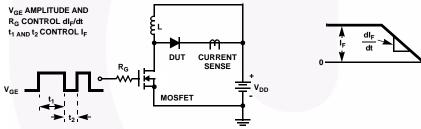


Figure 13. t_{rr} Test Circuit

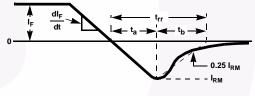


Figure 14. t_{rr} Waveforms and Definitions

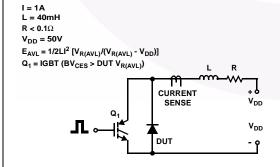


Figure 15. Avalanche Energy Test Circuit

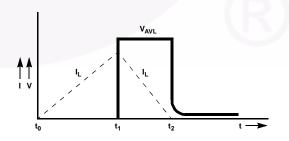


Figure 16. Avalanche Current and Voltage Waveforms

Mechanical Dimensions

TO247-2L

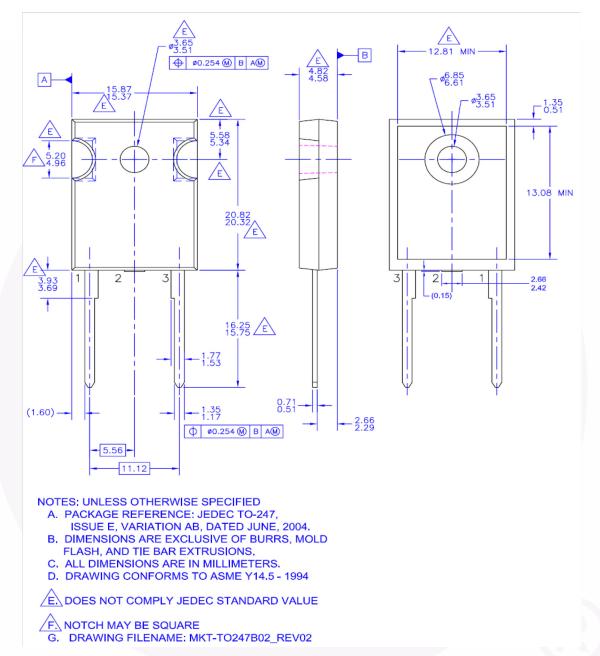


Figure 17. TO-247, Molded, 2LD, Jedec Option AB

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Rev. 166